



SANYO Semiconductors

DATA SHEET

CPH6444 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GS}		±20	V
Drain Current (DC)	I _D		4.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	18	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =2A	1.8	3		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =2A, V _{GS} =10V		60	78	mΩ
	R _{DS(on)2}	I _D =1A, V _{GS} =4.5V		74	104	mΩ
	R _{DS(on)3}	I _D =1A, V _{GS} =4V		81	114	mΩ

Marking : ZW

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

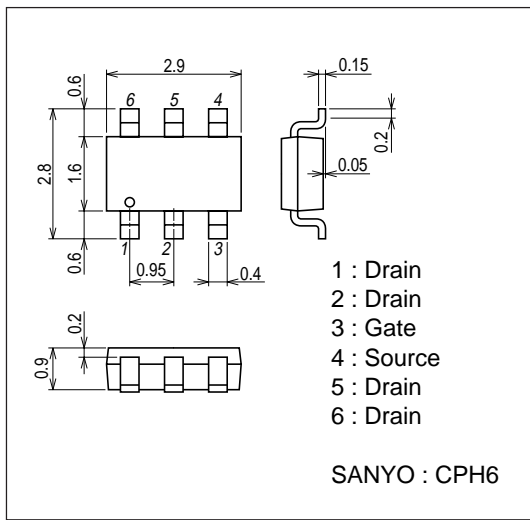
CPH6444

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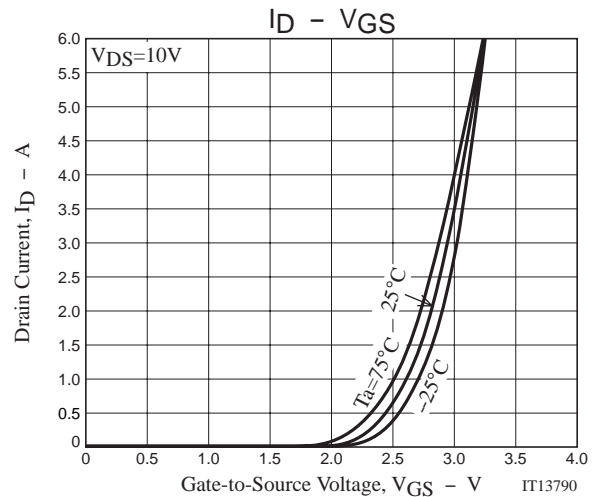
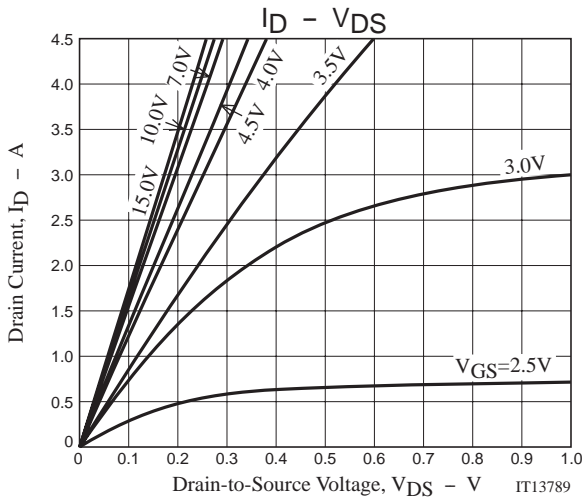
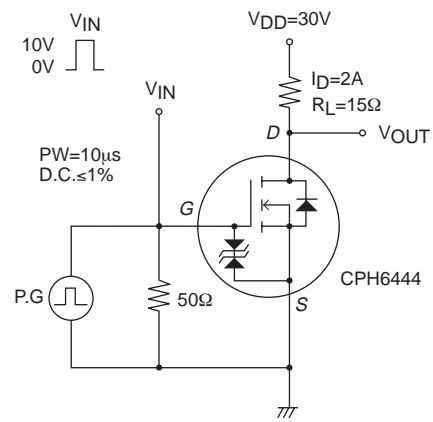
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		505		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		57		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		37		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		7.3		ns
Rise Time	t _r	See specified Test Circuit.		9.8		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		40		ns
Fall Time	t _f	See specified Test Circuit.		24		ns
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =10V, I _D =4.5A		10		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =30V, V _{GS} =10V, I _D =4.5A		1.6		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =30V, V _{GS} =10V, I _D =4.5A		2.1		nC
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.83	1.2	V

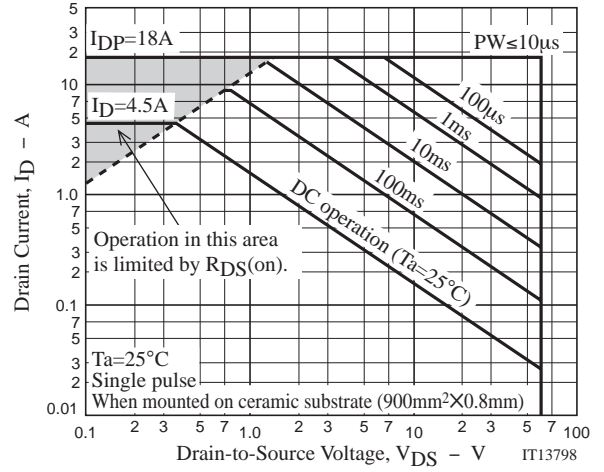
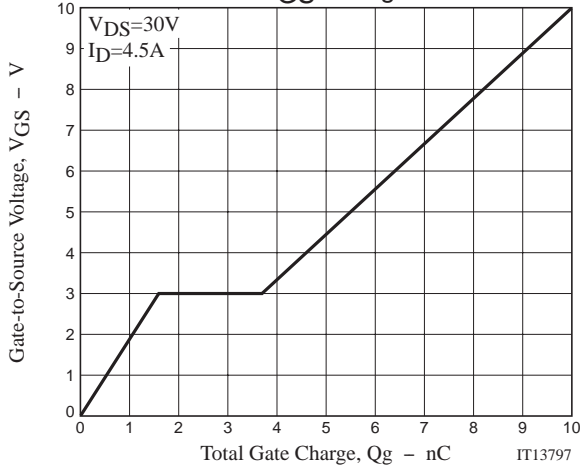
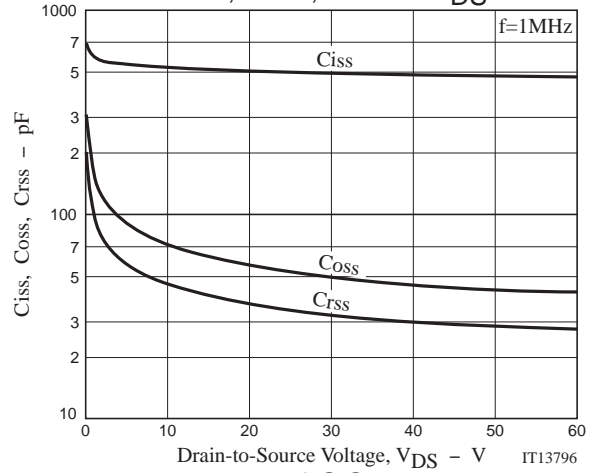
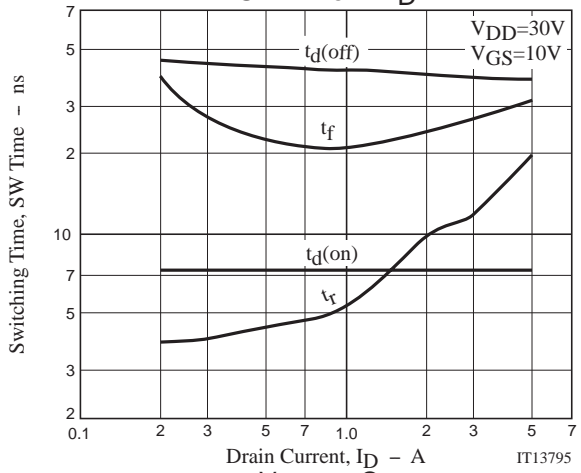
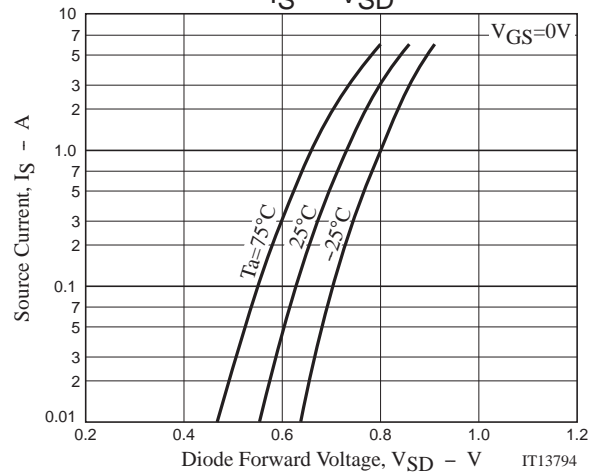
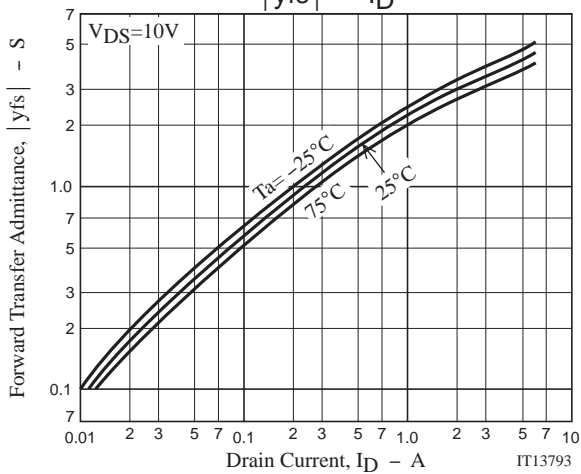
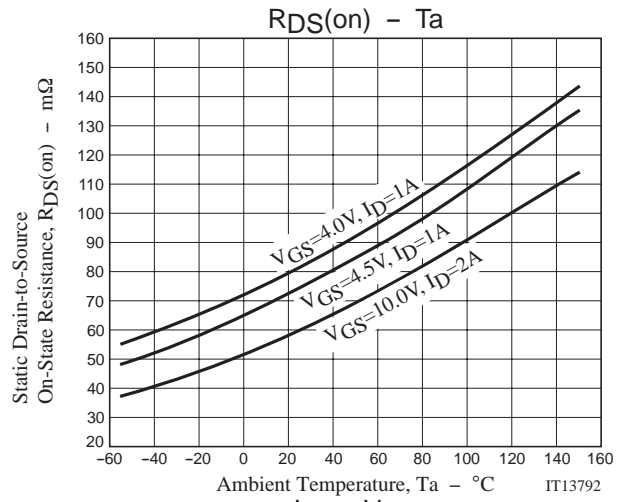
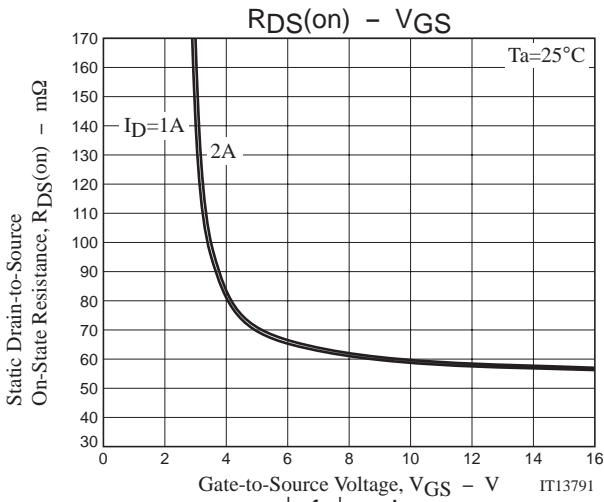
Package Dimensions

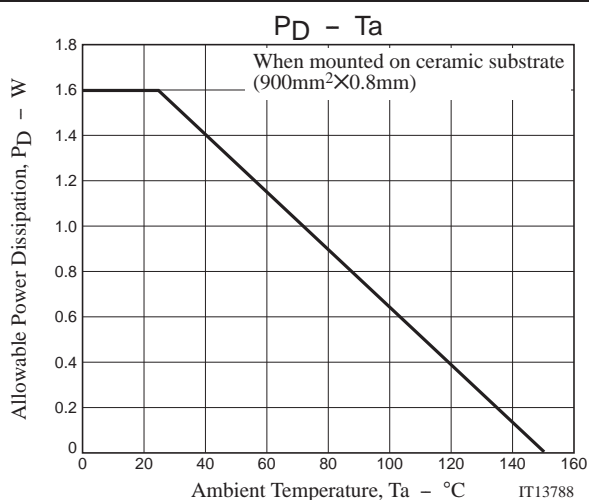
unit : mm (typ)
7018A-003



Switching Time Test Circuit







Note on usage : Since the CPH6444 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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